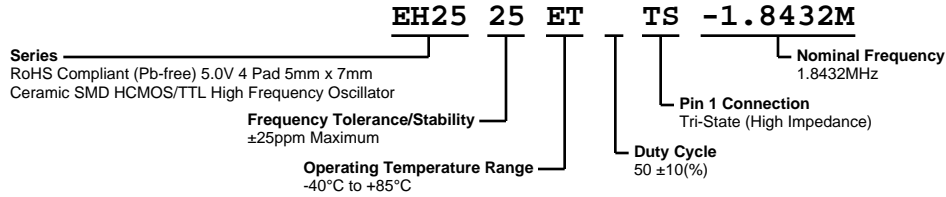


# EH2525ETTS-1.8432M



## ELECTRICAL SPECIFICATIONS

Nominal Frequency	1.8432MHz
Frequency Tolerance/Stability	±25ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C, Shock, and Vibration)
Aging at 25°C	±5ppm/year Maximum
Operating Temperature Range	-40°C to +85°C
Supply Voltage	5.0Vdc ±10%
Input Current	50mA Maximum (No Load)
Output Voltage Logic High (Voh)	2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load (IOH= -16mA)
Output Voltage Logic Low (Vol)	0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load (IOH= +16mA)
Rise/Fall Time	6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform with HCMOS Load)
Duty Cycle	50 ±10(%) (Measured at 1.4Vdc with TTL Load; Measured at 50% of waveform with HCMOS Load)
Load Drive Capability	10TTL Load or 50pF HCMOS Load Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (High Impedance)
Tri-State Input Voltage (Vih and Vil)	+2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output.
Absolute Clock Jitter	±250pSec Maximum, ±100pSec Typical
One Sigma Clock Period Jitter	±50pSec Maximum, ±30pSec Typical
Start Up Time	10mSec Maximum
Storage Temperature Range	-55°C to +125°C

## ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V
Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Flammability	UL94-V0
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-883, Method 2002, Condition B
Moisture Resistance	MIL-STD-883, Method 1004
Moisture Sensitivity	J-STD-020, MSL 1
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010, Condition B
Vibration	MIL-STD-883, Method 2007, Condition A

# EH2525ETTS-1.8432M

## MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	Tri-State
2	Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	<b>ECLIPTEK</b>
2	<b>1.8432M</b>
3	<b>XXXXXX</b> XXXXXX=Ecliptek Manufacturing Identifier

## Suggested Solder Pad Layout

All Dimensions in Millimeters



All Tolerances are  $\pm 0.1$

# EH2525ETTS-1.8432M

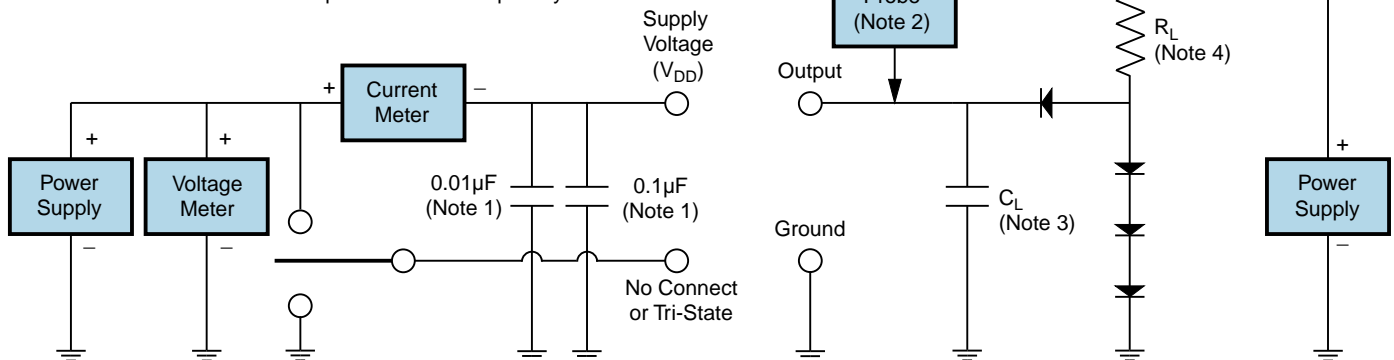
## OUTPUT WAVEFORM & TIMING DIAGRAM



### Test Circuit for TTL Output

Output Load Drive Capability	$R_L$ Value (Ohms)	$C_L$ Value (pF)
10TTL	390	15
5TTL	780	15
2TTL	1100	6
10LSTTL	2000	15
1TTL	2200	3

Table 1:  $R_L$  Resistance Value and  $C_L$  Capacitance Value Vs. Output Load Drive Capability



- Note 1: An external 0.1μF low frequency tantalum bypass capacitor in parallel with a 0.01μF high frequency ceramic bypass capacitor close to the package ground and  $V_{DD}$  pin is required.
- Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.
- Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.
- Note 4: Resistance value  $R_L$  is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.
- Note 5: All diodes are MMBD7000, MMBD914, or equivalent.

# EH2525ETTS-1.8432M

## Test Circuit for CMOS Output



Note 1: An external  $0.1\mu\text{F}$  low frequency tantalum bypass capacitor in parallel with a  $0.01\mu\text{F}$  high frequency ceramic bypass capacitor close to the package ground and  $V_{DD}$  pin is required.

Note 2: A low capacitance ( $<12\text{pF}$ ), 10X attenuation factor, high impedance ( $>10\text{Mohms}$ ), and high bandwidth ( $>300\text{MHz}$ ) passive probe is recommended.

Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.

## Recommended Solder Reflow Methods



### High Temperature Infrared/Convection

<b>T<sub>s</sub> MAX to T<sub>L</sub> (Ramp-up Rate)</b>	3°C/second Maximum
<b>Preheat</b>	
- Temperature Minimum (T <sub>s</sub> MIN)	150°C
- Temperature Typical (T <sub>s</sub> TYP)	175°C
- Temperature Maximum (T <sub>s</sub> MAX)	200°C
- Time (t <sub>s</sub> MIN)	60 - 180 Seconds
<b>Ramp-up Rate (T<sub>L</sub> to T<sub>p</sub>)</b>	3°C/second Maximum
<b>Time Maintained Above:</b>	
- Temperature (T <sub>L</sub> )	217°C
- Time (t <sub>L</sub> )	60 - 150 Seconds
<b>Peak Temperature (T<sub>p</sub>)</b>	260°C Maximum for 10 Seconds Maximum
<b>Target Peak Temperature (T<sub>p</sub> Target)</b>	250°C +0/-5°C
<b>Time within 5°C of actual peak (t<sub>p</sub>)</b>	20 - 40 seconds
<b>Ramp-down Rate</b>	6°C/second Maximum
<b>Time 25°C to Peak Temperature (t)</b>	8 minutes Maximum
<b>Moisture Sensitivity Level</b>	Level 1
<b>Additional Notes</b>	Temperatures shown are applied to body of device.

## Recommended Solder Reflow Methods



### Low Temperature Infrared/Convection 240°C

<b>T<sub>s</sub> MAX to T<sub>L</sub> (Ramp-up Rate)</b>	5°C/second Maximum
<b>Preheat</b>	
- Temperature Minimum (T <sub>s</sub> MIN)	N/A
- Temperature Typical (T <sub>s</sub> TYP)	150°C
- Temperature Maximum (T <sub>s</sub> MAX)	N/A
- Time (t <sub>s</sub> MIN)	60 - 120 Seconds
<b>Ramp-up Rate (T<sub>L</sub> to T<sub>P</sub>)</b>	5°C/second Maximum
<b>Time Maintained Above:</b>	
- Temperature (T <sub>L</sub> )	150°C
- Time (t <sub>L</sub> )	200 Seconds Maximum
<b>Peak Temperature (T<sub>P</sub>)</b>	240°C Maximum
<b>Target Peak Temperature (T<sub>P</sub> Target)</b>	240°C Maximum 1 Time / 230°C Maximum 2 Times
<b>Time within 5°C of actual peak (t<sub>p</sub>)</b>	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
<b>Ramp-down Rate</b>	5°C/second Maximum
<b>Time 25°C to Peak Temperature (t)</b>	N/A
<b>Moisture Sensitivity Level</b>	Level 1
<b>Additional Notes</b>	Temperatures shown are applied to body of device.

### Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

### High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)